ONET2804TLP
Low-Power, 28-Gbps, 4-Channel Limiting TIA

1 Features

- 4-Channel Multi-Rate Operation: Up to 28 Gbps
- Dissipation at a 3-V Supply: 90 mW per Channel
- Differential Transimpedance: 7.5 kΩ
- Bandwidth: 17.5 GHz
- Input-Referred Noise: 2 μA_{rms}
- Input Overload Current: 3.2 mA_{PP}
- Programmable Output Voltage
- Adjustable Gain and Bandwidth
- Received Signal Strength Indicator (RSSI) for Each Channel
- Isolation Between Channels (Die Only): 40 dB
- Single Supply: 2.8 V to 3.3 V
- Pad Control or 2-Wire Control
- On-Chip Filter Capacitors
- –40°C to +100°C Operation
- Die Size: 3250 µm × 1450 µm, 750-µm Channel Pitch

2 Applications

- 100 Gigabit Ethernet Optical Receivers
- ITU OTL4.4
- CFP2, CFP4, and QSFP28 Modules with Internal Retiming

3 Description

The ONET2804TLP device is a high-gain, limiting transimpedance amplifier (TIA) for parallel optical interconnects with data rates up to 28 Gbps. The device is used in conjunction with a 750-µm pitch photodiode array to convert an optical signal into a differential output voltage. An internal circuit provides the photodiode reverse bias voltage and senses the average photocurrent supplied to each photodiode.

The device can be used with pin control or a two-wire serial interface to allow control of the output amplitude, gain, bandwidth, and input threshold.

The ONET2804TLP provides 17.5-GHz bandwidth, a gain of 7.5 kΩ, an input-referred noise of 2 μA_{rms}, and a received signal strength indicator (RSSI) for each channel. 40-dB isolation between channels results in low crosstalk penalty in the receiver.

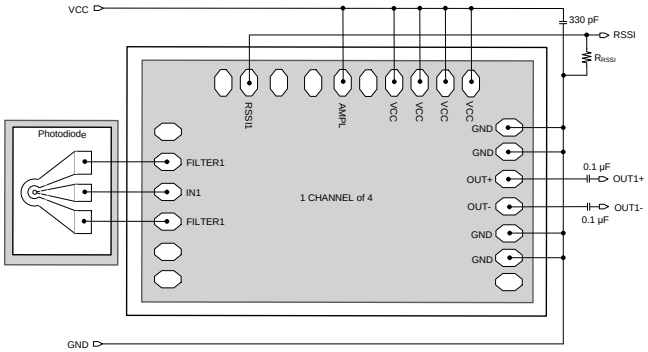
The device requires a single 2.8-V to 3.3-V supply and typically dissipates 90 mW per channel with a differential output amplitude of 300 mV_{PP}. The device is characterized for operation from –40°C to +100°C and is available in die form with a 750-µm channel pitch.

Device Information(1)

PART NUMBER	PACKAGE	BODY SIZE (NOM)
ONET2804TLP	Base Die in Waffle Pack	3250 µm × 1450 µm

(1) For all available packages, see the orderable addendum at the end of the datasheet.

Simplified Schematic



Eye Diagram

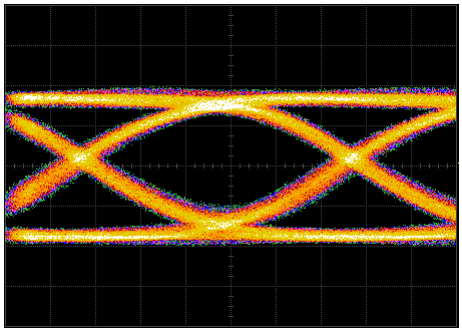


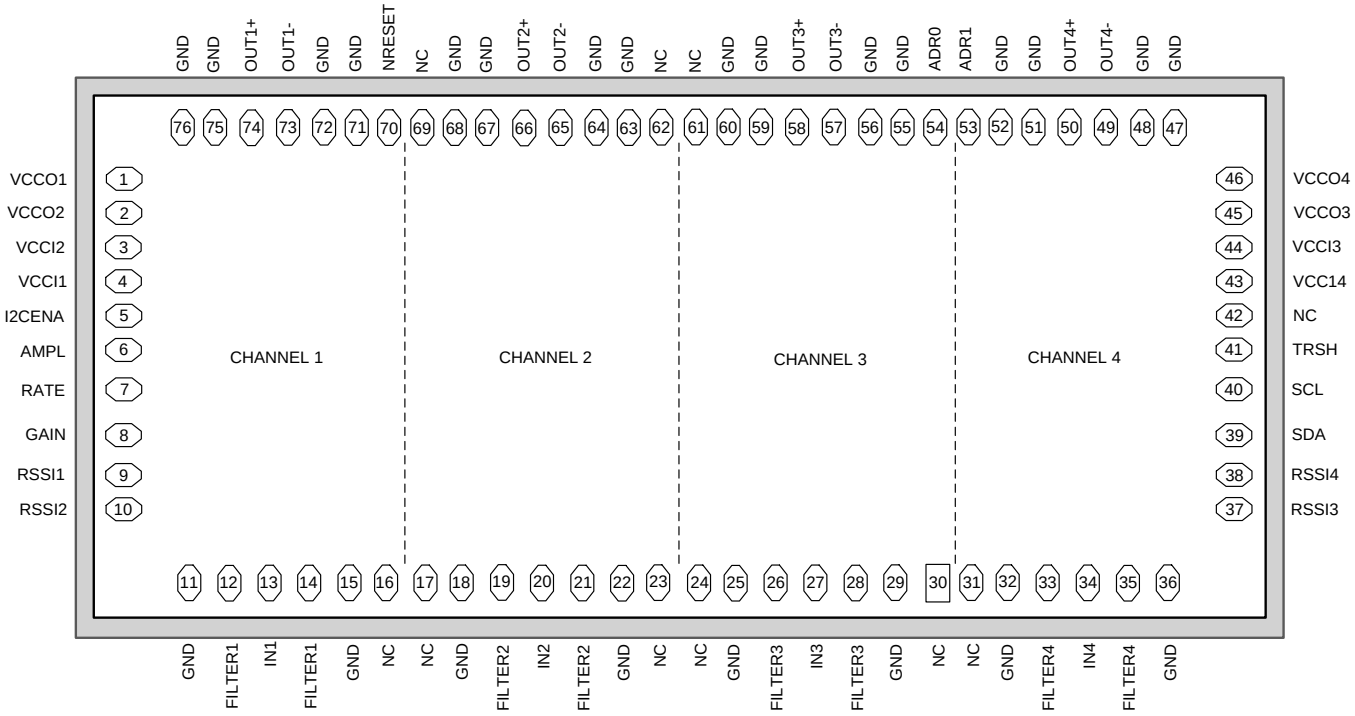
Table of Contents

4 Revision History

DATE	REVISION	NOTES
July 2017	*	Initial release.

5 Pin Configuration and Functions

ONET2804TLP Bond Pad Assignment: Y Package
76-Pad Die
Top View



Bond Pad Functions

PAD		I/O	DESCRIPTION
NAME	NO.		
ADR0	54	Digital input	2-wire interface address programming pin. Leave this pad open for a default address of 0001100. Grounding this pad changes the first address bit to a 1 (0001101).
ADR1	53	Digital input	2-wire interface address programming pin. Leave this pad open for a default address of 0001100. Grounding this pad changes the second address bit to a 1 (0001110).
AMPL	6	Digital input	3-state input for amplitude control of all four channels. V_{CC}: 500-mV_{PP} differential output swing Open: 300-mV_{PP} differential output swing (default) GND: 250-mV_{PP} differential output swing
FILTER1	12, 14	Analog output	FILTERx is the bias voltage for the photodiode cathode. These pads are biased to V_{CC} – 100 mV.
FILTER2	19, 21		
FILTER3	26, 28		
FILTER4	33, 35		
GAIN	8	Digital input	3-state input for gain control of all four channels. V_{CC}: Minimum transimpedance Open: Default transimpedance GND: Medium transimpedance
GND	11, 15, 18, 22, 25, 29, 32, 36, 47, 48, 51, 52, 55, 56, 59, 60, 63, 64, 67, 68, 71, 72, 75, 76	Supply	Circuit ground. All GND pads are connected on the die. Bonding all pads is recommended, except for pads 11, 15, 18, 22, 25, 29, 32, and 36.

Bond Pad Functions (continued)

PAD		I/O	DESCRIPTION
NAME	NO.		
I2CENA	5	Digital input	2-wire control option. Leave the pad unconnected for pad control of the device. Two-wire control can be enabled by applying a high signal to the pad.
IN1	13	Analog input	INx is the data input to corresponding TIA channel (connect to photodiode anode)
IN2	20		
IN3	27		
IN4	34		
NC	16, 17, 23, 24, 30, 31, 42, 61, 62, 69	No connection	Do not connect
NRESET	70	Digital input	Used to reset the 2-wire state machine and registers. Leave open for normal operation and set low to reset the 2-wire interface.
OUT1–	73	Analog output	Inverted CML data output for channel x. On-chip, 50-Ω, back-terminated to V_{CC}.
OUT2–	65		
OUT3–	57		
OUT4–	49		
OUT1+	74	Analog output	Noninverted CML data output for channel x. On-chip, 50-Ω, back-terminated to V_{CC}.
OUT2+	66		
OUT3+	58		
OUT4+	50		
RATE	7	Digital input	3-state input for bandwidth control of all four channels. V_{CC}: Increase the bandwidth Open: 21-GHz bandwidth (default) GND: Reduce the bandwidth
RSSI1	9	Analog output	Indicates the strength of the received signal (RSSI) for channel x if the photodiode is biased from FILTERx. The analog output current is proportional to the input data amplitude. Connect to an external resistor to ground (GND). For proper operation, ensure that the voltage at the RSSIx pad does not exceed V_{CC} – 0.65 V. If the RSSI feature is not used, leave these pads open.
RSSI2	10		
RSSI3	37		
RSSI4	38		
SCL	40	Digital input	2-wire interface serial clock input. Includes a 10-kΩ pullup resistor to V_{CC}.
SDA	39	Digital input/output	2-wire interface serial data input. Includes a 10-kΩ pullup resistor to V_{CC}.
TRSH	41	Digital input	3-state input for the threshold control. V_{CC}: Crossing point shifted down Open: No threshold adjustment (default) GND: Crossing point shifted up
$V_{CC}I1$	4	Supply	2.8 V to 3.47 V supply voltage for the input TIAx stage.
$V_{CC}I2$	3		
$V_{CC}I3$	44		
$V_{CC}I4$	43		
$V_{CC}O1$	1	Supply	2.8 V to 3.47 V supply voltage for the AGCx and CMLx amplifiers.
$V_{CC}O2$	2		
$V_{CC}O3$	45		
$V_{CC}O4$	46		

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

		MIN	MAX	UNIT
Supply voltage(1)	V_{CC}Ix, V_{CC}Ox	–0.3	4	V
Voltage(1)	FILTERx, OUTx+, OUTx–, RSSIx, SCL, SDA, I2CENA, ICC_ADJ, AMPL, RATE, GAIN, TRSH, ADR1, ADR0, and NRESET	–0.3	4	V
Average input current	INx	–0.7	5	mA
	FILTERx	–8	8	mA
Continuous current at outputs	OUTx+, OUTx–	–8	8	mA
Maximum junction temperature, T_J			125	°C
Storage temperature, T_{stg}		–65	150	°C

(1) All voltage values are with respect to network ground terminal.

6.2 ESD Ratings

				VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001(1)	All pins except INx	±1000	V
			INx pins	±500	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

			MIN	NOM	MAX	UNIT
V_{CC}	Supply voltage		2.8	3.3	3.47	V
$I_{(INx)}$	Average input current				2.7	mA
T_A	Operating backside die temperature		–40		100	°C
$L_{(FILTER)}$, $L_{(IN)}$	Wire-bond inductance at the FILTERx and INx pins			0.3		nH
$C_{(PD)}$	Photodiode capacitance			0.1		pF
V_{IH}	Digital input high voltage	SDA, SCL	2			V
V_{IL}	Digital input low voltage	SDA, SCL			0.8	V
	3-state input high voltage		V_{CC} – 0.4			V
	3-state input low voltage				0.4	V

6.4 DC Electrical Characteristics

over recommended operating conditions with V_{OD} = 300 mV_{PP} (unless otherwise noted); typical values are at V_{CC} = 3.3 V and T_A = 25°C

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT	TEST LEVEL(1)
V_{CC}	Supply voltage		2.8	3.3	3.47	V	A
I_{CC}	Supply current	Per channel, 30-μA_{PP} input, 27°C	22		42	mA	A
		Per channel, 30-μA_{PP} input, maximum 85°C		30			C
		Per channel, 30-μA_{PP} input, maximum 100°C		36			C
$P_{(RX)}$	Receiver power dissipation	Per channel, 30-μA_{PP} input, 27°C	73		139	mW	A
		Per channel, 30-μA_{PP} input, maximum 85°C		99			C
		Per channel, 30-μA_{PP} input, maximum 100°C		118			C
V_{IN}	Input bias voltage		0.75	0.85	0.98	V	A
R_{OUT}	Output resistance	Single-ended to V_{CC}	40	50	60	Ω	A
$V_{(FILTER)}$	Photodiode bias voltage(2)		2.8	3.2		V	A
$A_{(RSSI\_IB)}$	RSSI gain	Resistive load to GND(3)	0.49	0.5	0.54	A/A	A
	RSSIx feature output offset current (no light)		0		2.5	µA	A

(1) Test levels: (A) 100% tested at 25°C. Overtemperature limits set by characterization and simulation. (B) Limits set by characterization and simulation. (C) Typical value only for information.
(2) Regulated voltage is typically 100 mV lower than V_{CC}.
(3) The RSSIx output is a current output that requires a resistive load to ground (GND). The voltage gain can be adjusted for the intended application by choosing the external resistor; however, for proper operation, ensure that the voltage at RSSIx does not exceed V_{CC} – 0.65 V.

6.5 AC Electrical Characteristics

over recommended operating conditions with V_{OD} = 300 mV_{PP} (unless otherwise noted); typical values are at V_{CC} = 3.3 V and T_A = 25°C

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT	TEST LEVEL(1)
Z_{21}	Small-signal transimpedance	25-μA_{PP} input signal		7.5		kΩ	C
$f_{(3dB-H)}$	–3-dB bandwidth	25-μA_{PP} input signal(2)		17.5		GHz	C
$f_{(3dB-L)}$	Low-frequency, –3-dB bandwidth			30		kHz	C
$i_{N(IN)}$	Input-referred RMS noise	CPD = 0.1 pF, 28-GHz BT4 filter(3)		2		µA	C
DJ	Deterministic jitter	35 $\mu A_{PP} < i_{IN} < 250\ \mu A_{PP}$ (27.95 Gbps, PRBS9 pattern)		2		ps_{PP}	C
		250 $\mu A_{PP} < i_{IN} < 500\ \mu A_{PP}$ (27.95 Gbps, PRBS9 pattern)		2			C
		500 $\mu A_{PP} < i_{IN} < 2900\ \mu A_{PP}$ (27.95 Gbps, PRBS9 pattern)		4			C
V_{OD}	Differential output voltage	500-mV_{PP} setting	250	500	700	mV_{PP}	C
	Crosstalk	Between adjacent channels, up to 20 GHz(4)		–40		dB	C
	RSSIx response time			1		µs	C
PSRR	Power-supply rejection ratio	f < 10 MHz(5)		–15		dB	C

(1) Test levels: (A) 100% tested at 25°C. Overtemperature limits set by characterization and simulation. (B) Limits set by characterization and simulation. (C) Typical value only for information.
(2) The small-signal bandwidth is specified over process corners, temperature, and supply voltage variation. The assumed photodiode capacitance is 0.1 pF and the bond-wire inductance is 0.3 nH. The small-signal bandwidth strongly depends on environmental parasitics. Careful attention to layout parasitics and external components is necessary to achieve optimal performance.
(3) Input-referred RMS noise is (RMS output noise) / (gain at 100 MHz).
(4) Die only, no wire bonds.
(5) PSRR is the differential output amplitude divided by the voltage ripple on the supply. No input current at INx.

6.6 Timing Requirements

		MIN	NOM	MAX	UNIT
f_{SCK}	SCK clock frequency			400	kHz
t_{BUF}	Bus free time between START and STOP conditions	1.3			µs
t_{HDSTA}	Hold time after repeated START condition. After this period, the first clock pulse is generated.	0.6			µs
t_{LOW}	Low period of the SCK clock	1.3			µs
t_{HIGH}	High period of the SCK clock	0.6			µs
t_{SUSTA}	Setup time for a repeated START condition	0.6			µs
t_{HDDAT}	Data hold time	0			µs
t_{SUDAT}	Data setup time	100			ns
t_R	Rise time of both SDA and SCK signals			300	ns
t_F	Fall time of both SDA and SCK signals			300	ns
t_{SUSTO}	Setup time for STOP condition	0.6			µs

6.7 Typical Characteristics: General

typical operating condition is at V_{CC} = 3.3 V, T_A = 25°C, and V_{OD} = 300 mV_{PP} (unless otherwise noted)

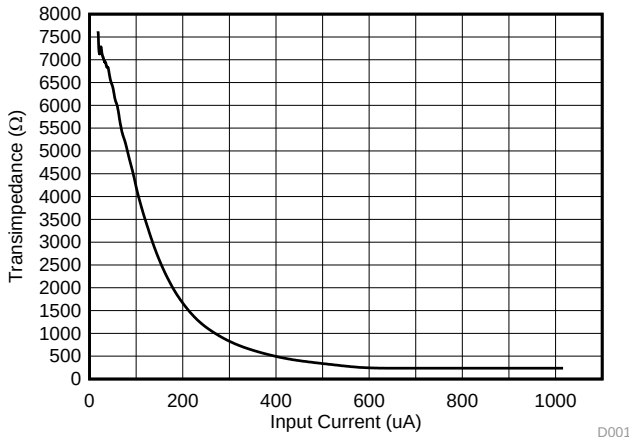


Figure 1. Transimpedance vs Input Current

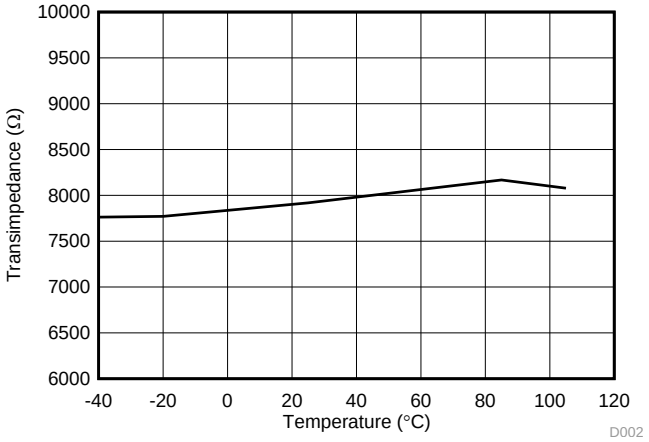


Figure 2. Small-Signal Transimpedance vs Ambient Temperature

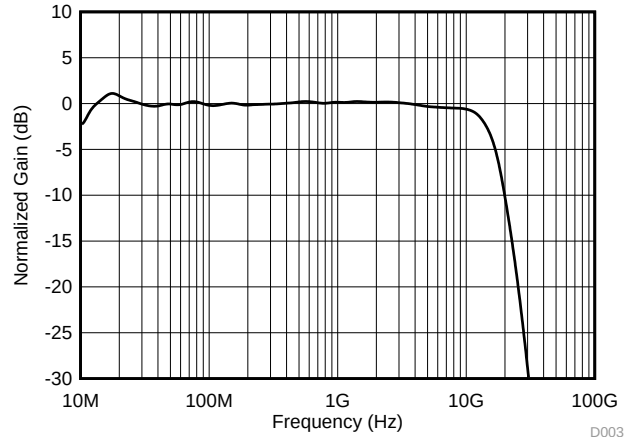


Figure 3. Gain vs Frequency (Test Fixture Loss De-Embedded)

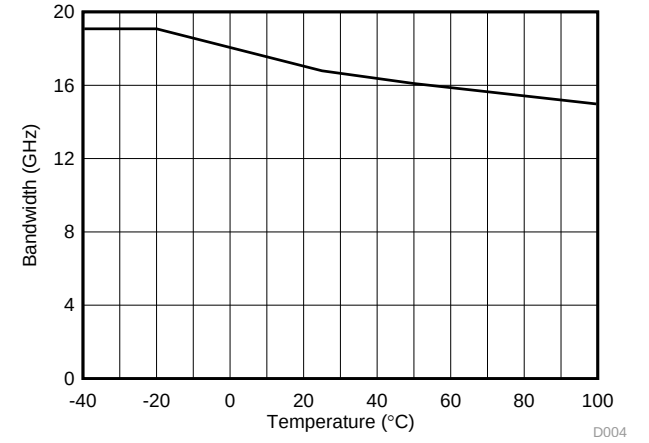


Figure 4. Small-Signal Bandwidth vs Ambient Temperature (Test Fixture Loss De-Embedded)

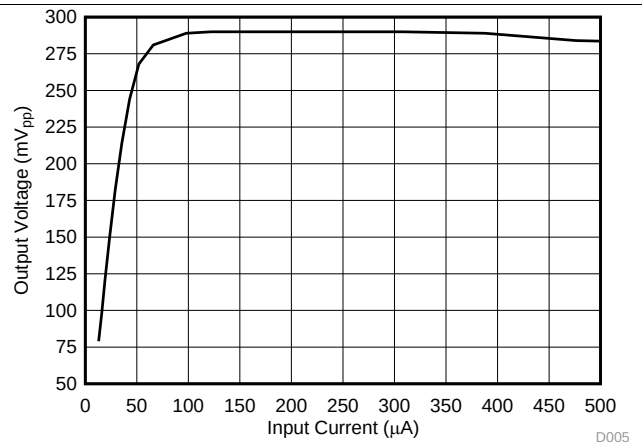


Figure 5. Differential Output Voltage vs Input Current

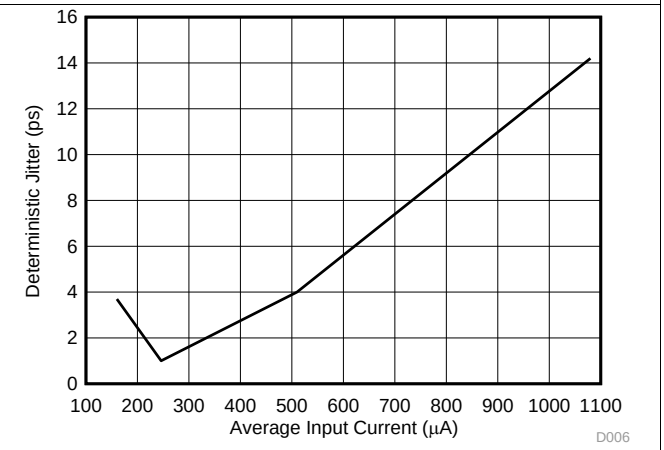


Figure 6. Deterministic Jitter vs Input Current

Typical Characteristics: General (continued)

typical operating condition is at V_{CC} = 3.3 V, T_A = 25°C, and V_{OD} = 300 mV_{PP} (unless otherwise noted)

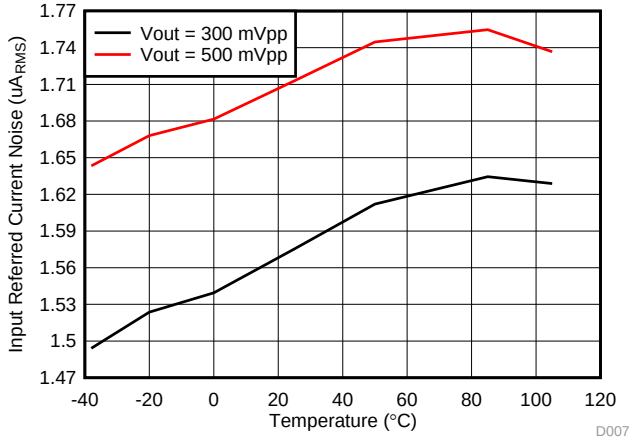


Figure 7. Input-Referred Noise vs Ambient Temperature

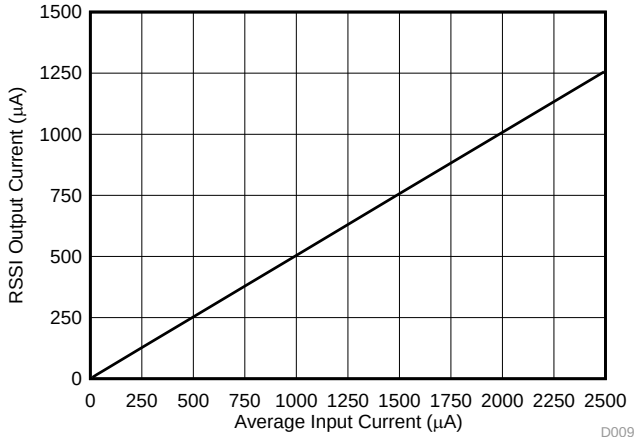
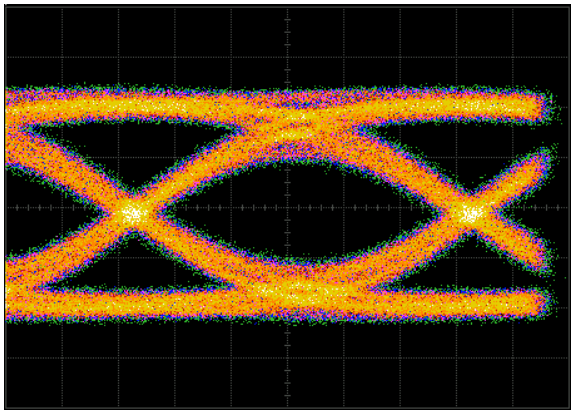


Figure 8. RSSIx Output Current vs Average Input Current

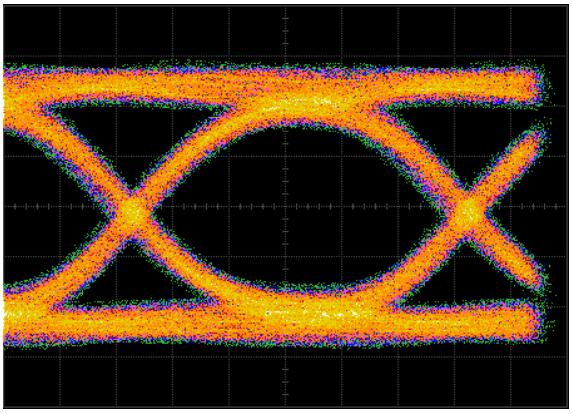
6.8 Typical Characteristics: Eye Diagrams

typical operating condition is at V_{CC} = 3.3 V, T_A = 25°C, and V_{OD} = 500 mV_{PP} (unless otherwise noted)



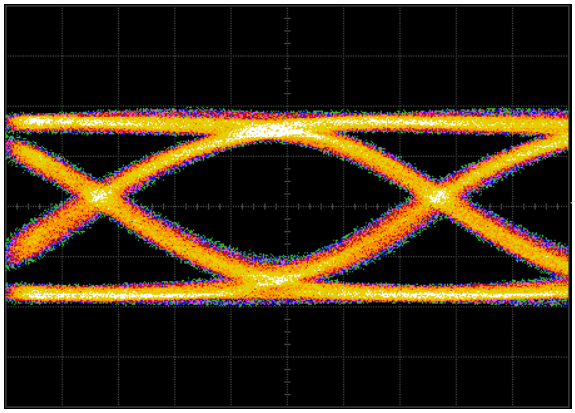
27.95 Gbps

Figure 9. Output Eye-Diagram, 30-μA_{PP} Input Current



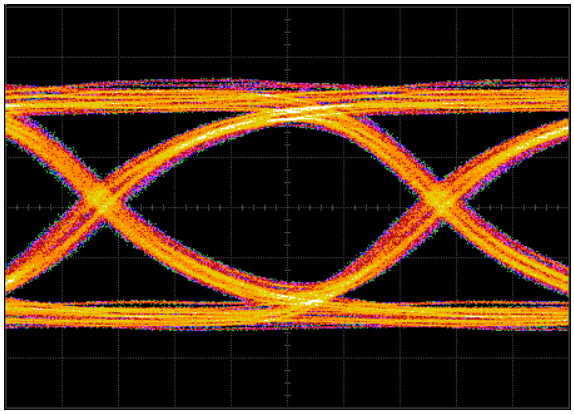
27.95 Gbps

Figure 10. Output Eye-Diagram, 500-μA_{PP} Input Current



27.95 Gbps

Figure 11. Output Eye-Diagram, 1.5-mA_{PP} Input Current



27.95 Gbps

Figure 12. Output Eye-Diagram, 2.5-mA_{PP} Input Current

7 Detailed Description

7.1 Overview

The *Functional Block Diagram* section shows a simplified block diagram for one channel of the ONET2804TLP.

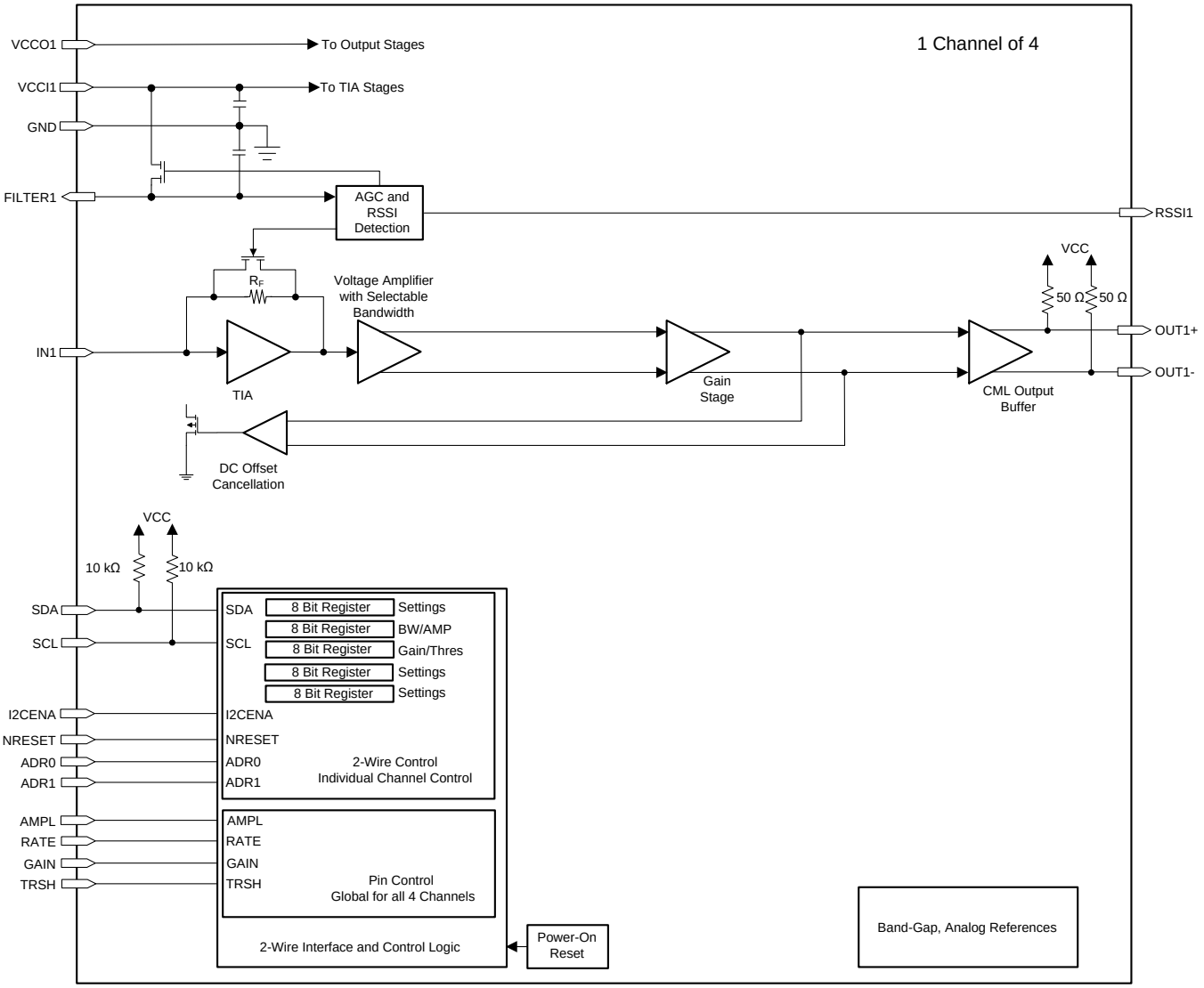
The ONET2804TLP consists of the signal path, supply filters, a control block for dc input bias, automatic gain control (AGC) and received signal strength indication (RSSI), an analog reference block and a two-wire serial interface and control logic block.

The signal path consists of a transimpedance amplifier (TIA) stage, a voltage amplifier, and a current-mode logic (CML) output buffer. The on-chip filter circuit provides a filtered V_{CC} for the PIN photodiode and for the transimpedance amplifier. The RSSI provides the bias for the TIA stage and control for the AGC.

The DC input bias circuit and automatic gain control use internal low-pass filters to cancel the DC current on the input and to adjust the transimpedance amplifier gain. Furthermore, circuitry is provided to monitor the received signal strength.

The output amplitude, gain, bandwidth, and input threshold can be globally controlled through pin settings or each channel can be individually controlled through the two-wire interface.

7.2 Functional Block Diagram



7.3 Feature Description

7.3.1 Signal Path

The first stage of the signal path is a transimpedance amplifier that converts the photodiode current into a voltage. If the input signal current exceeds a certain value, the transimpedance gain is reduced by means of a nonlinear AGC circuit to limit the signal amplitude.

The second stage is a limiting voltage amplifier that provides additional limiting gain and converts the single-ended input voltage into a differential data signal. The output stage provides CML outputs with an on-chip, 50-Ω termination to V_{CC}.

The TIA has adjustable gain, amplitude, bandwidth, and input threshold that can be globally controlled through pad settings or each channel can be individually controlled through the two-wire interface. The default mode of operation is pad control where the state (open, high, or low) of the AMPL, BW, GAIN, and TRSH pads sets the respective parameter. To enable two-wire control, set the I2CENA pad high and the functionality of each channel can be controlled individually through the two-wire interface.

7.3.2 Gain Adjustment

The gain of all TIAs can be adjusted using the GAIN pad (pad 8) in pad control mode. Gain is set to default if the pad is left open. Gain is reduced by approximately 4 dB if the pad is tied to ground, and reduced by approximately 8 dB if the pad is tied to V_{CC}. In two-wire control mode, the gain of each channel can be adjusted from minimum to default. Gain is controlled with the GAIN[1:0] bits in registers 2, 8, 14, and 20 for channels 1, 2, 3, and 4, respectively.

7.3.3 Amplitude Adjustment

The output amplifier of all buffers can be adjusted using the AMPL pad (pad 6) in pad control mode. The amplitude is set to 300 mV_{PP} differential if the pad is left open, 250 mV_{PP} if the pad is tied to ground, and 450 mV_{PP} if the pad is tied to V_{CC} voltage (recommended mode of operation). In two-wire control mode, the amplitude of each channel can be adjusted from 0 mV_{PP} to 600 mV_{PP}. The amplitude is controlled with the AMPL[3:0] bits in registers 1, 7, 13, and 19 for channels 1, 2, 3, and 4, respectively.

7.3.4 Rate Select

The small-signal bandwidth can be adjusted using the RATE pad (pad 7) in pad control mode. Bandwidth is typically 20 GHz if the pad is left open. Bandwidth is reduced by approximately 0.4 GHz if the pad is tied to ground, and increased by approximately 0.4 GHz if the pad is tied to V_{CC}. In two-wire control mode, the bandwidth of each channel can be adjusted up or down using the RATE[3:0] register settings in registers 1, 7, 13, and 19 for channels 1, 2, 3, and 4, respectively.

7.3.5 Threshold Adjustment

The TIAs have DC offset cancellation to maintain a 50% crossing point; however, the crossing point can be adjusted using the TRSH pad (pad 41) in pad control mode. No threshold adjustment is applied if the pad is left open. The crossing point is shifted up approximately 12% if the pad is tied to ground, and is shifted down by approximately 12% if the pad is tied to V_{CC}. In two-wire control mode, the crossing point can be adjusted up or down using the TH[3:0] register settings in registers 2, 8, 14, and 20 for channels 1, 2, 3, and 4, respectively.

7.3.6 Filter Circuitry

The FILTERx pins provide a regulated and filtered V_{CC} for a PIN photodiode bias. The supply voltages for the transimpedance amplifier have on-chip capacitors but external filter capacitors are recommended to be used as well for best performance. The input stage has a separate V_{CC} supply (V_{CC}Ix) that is not connected on-chip to the supply of the limiting and CML stages (V_{CC}Ox).

7.3.7 AGC and RSSI

The voltage drop across the regulated photodiode FET is monitored by the bias and RSSI control circuit block in the case where a PIN diode is biased using the FILTERx pins.

Feature Description (continued)

If the DC input current exceeds a certain level then this current is partially cancelled by means of a controlled current source. This cancellation keeps the transimpedance amplifier stage within sufficient operating limits for optimum performance.

The automatic gain control circuitry adjusts the voltage gain of the AGC amplifier to ensure limiting behavior of the complete amplifier.

Finally, this circuit block senses the current through the FILTERx FET and generates a mirrored current that is proportional to the input signal strength. The mirrored currents are available at the RSSIx outputs and can be sunk to ground (GND) using an external resistor. For proper operation, ensure that the voltage at the RSSIx pad does not exceed V_{CC} – 0.65 V.

7.4 Device Functional Modes

The device has two functional modes of operation: pad control mode and two-wire interface control mode.

7.4.1 Pad Control

The default mode of operation is pad control and the amplitude is recommended to be increased to the 450 mV_{PP} setting by bonding AMPL (pad 6) to V_{CC}. If further adjustment is desired as described previously, then the RATE (pad 7), GAIN (pad 8), and TRSH (pad 41) control pads and can be bonded to either ground (GND) or V_{CC}.

7.4.2 Two-Wire Interface Control

To enable two-wire interface, the I2CENA (pad 5) control pad must be bonded to V_{CC}. In this mode of operation, pad control is not functional and all control is initiated through the two-wire interface as described in the *Programming* section.

7.5 Programming

The ONET2804TLP uses a two-wire serial interface for digital control. For example, the two circuit inputs (SDA and SCK) are driven by the serial data and serial clock from a microcontroller. Both inputs include 10-kΩ pullup resistors to V_{CC}. For driving these inputs, an open-drain output is recommended. The two-wire interface allows write access to the internal memory map to modify control registers and read access to read out control and status signals. The ONET2804TLP is a slave device only, which means that the device cannot initiate a transmission, but always relies on the availability of the SCK signal for the duration of the transmission. The master device provides the clock signal as well as the START and STOP commands. The device is recommended to be used on a bus with only one master. The protocol for a data transmission is as follows:

1. START command
2. 7-bit slave address (0001100) followed by an eighth bit that is the data direction bit (R/W). A zero indicates a write operation and a 1 indicates a read operation.
3. 8-bit register address
4. 8-bit register data word
5. STOP command

Regarding timing, the ONET2804TLP is I^2C compatible. Figure 13 illustrates the typical timing and Figure 14 illustrates a complete data transfer. Parameters for Figure 13 are defined in the *Timing Requirements* table.

Programming (continued)

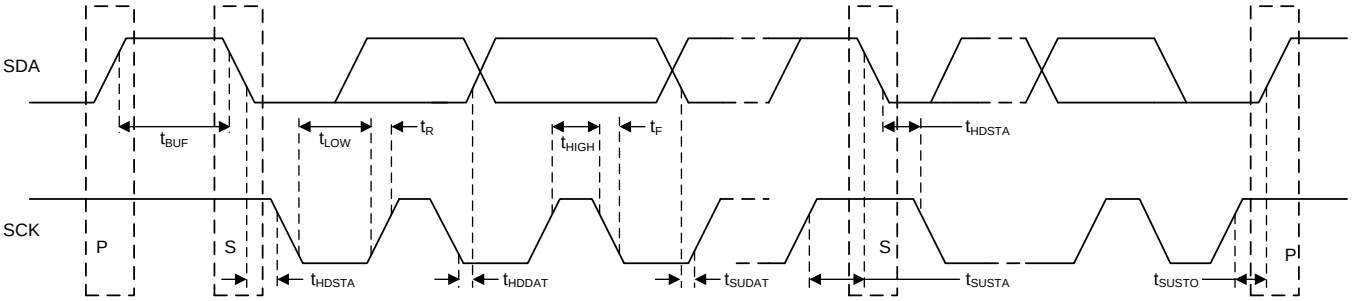


Figure 13. I²C Timing Diagram

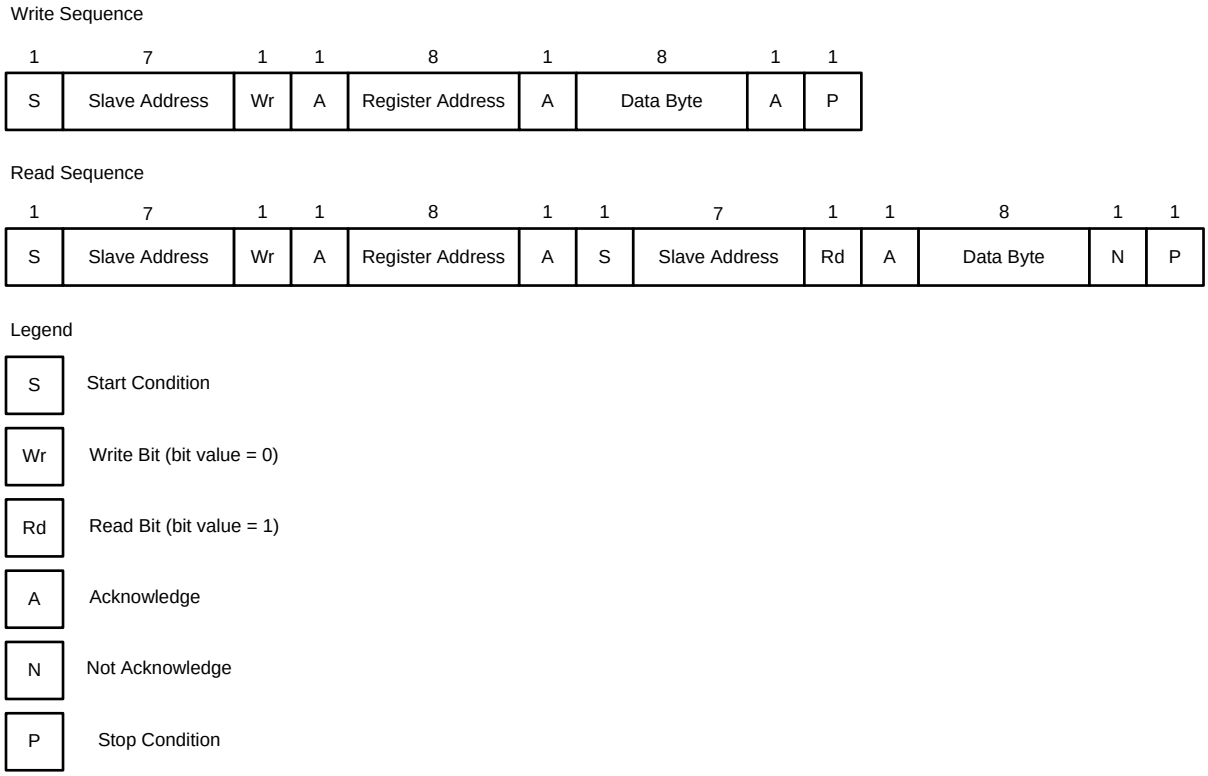


Figure 14. Data Transfer

7.5.1 Bus Idle

Both the SDA and SCK lines remain high.

7.5.2 Start Data Transfer

A change in the state of the SDA line from high to low when the SCK line is high defines a START condition (S). Each data transfer is initiated with a START condition.

7.5.3 Stop Data Transfer

A change in the state of the SDA line from low to high when the SCK line is high defines a STOP condition (P). Each data transfer is terminated with a STOP condition; however, to continue communication on the bus, the master can generate a repeated START condition and address another slave without first generating a STOP condition.

Programming (continued)

7.5.4 Data Transfer

Only one data byte can be transferred between a START and a STOP condition. The receiver acknowledges the transfer of data.

7.5.5 Acknowledge

Each receiving device, when addressed, is obliged to generate an acknowledge bit. The transmitter releases the SDA line and a device that acknowledges must pull down the SDA line during the acknowledge clock pulse in such a way that the SDA line is stable low during the high period of the acknowledge clock pulse. Setup and hold times must be taken into account. When a slave-receiver does not acknowledge the slave address, the data line must be left high by the slave. The master can then generate a STOP condition to abort the transfer. If the slave-receiver does acknowledge the slave address but some time later in the transfer cannot receive any more data bytes, the master must abort the transfer. This requirement is indicated by the slave generating a not acknowledge on the first subsequent byte. The slave leaves the data line high and the master generates the STOP condition.

7.6 Register Maps

Table 1 lists the registers for the ONET2804TLP.

Table 1. Register Map

REGISTER		REGISTER DATA							
NAME	ADDRESS	7	6	5	4	3	2	1	0
Register 0	00h	RESET	PD	RESERVED	RESERVED	RESERVED	RESERVED	RESERVED	PWRITE
Register 1	01h	RATE3	RATE2	RATE1	RATE0	AMP3	AMP2	AMP1	AMP0
Register 2	02h	PD	DIS	GAIN1	GAIN0	TH3	TH2	TH1	TH0
Register 3	03h	RESERVED	RESERVED	RESERVED	RESERVED	RESERVED	RESERVED	RESERVED	RESERVED
Register 4	04h	RESERVED	RESERVED	RESERVED	RESERVED	RESERVED	RESERVED	RESERVED	RESERVED
Register 5	05h	RESERVED	RESERVED	RESERVED	RESERVED	RESERVED	RESERVED	RESERVED	RESERVED
Register 6	06h	RESERVED	RESERVED	RESERVED	RESERVED	RESERVED	RESERVED	RESERVED	RESERVED
Register 7	07h	RATE3	RATE2	RATE1	RATE0	AMP3	AMP2	AMP1	AMP0
Register 8	08h	PD	DIS	GAIN1	GAIN0	TH3	TH2	TH1	TH0
Register 9	09h	RESERVED	RESERVED	RESERVED	RESERVED	RESERVED	RESERVED	RESERVED	RESERVED
Register 10	0Ah	RESERVED	RESERVED	RESERVED	RESERVED	RESERVED	RESERVED	RESERVED	RESERVED
Register 11	0Bh	RESERVED	RESERVED	RESERVED	RESERVED	RESERVED	RESERVED	RESERVED	RESERVED
Register 12	0Ch	RESERVED	RESERVED	RESERVED	RESERVED	RESERVED	RESERVED	RESERVED	RESERVED
Register 13	0Dh	RATE3	RATE2	RATE1	RATE0	AMP3	AMP2	AMP1	AMP0
Register 14	0Eh	PD	DIS	GAIN1	GAIN0	TH3	TH2	TH1	TH0
Register 15	0Fh	RESERVED	RESERVED	RESERVED	RESERVED	RESERVED	RESERVED	RESERVED	RESERVED
Register 16	10h	RESERVED	RESERVED	RESERVED	RESERVED	RESERVED	RESERVED	RESERVED	RESERVED
Register 17	11h	RESERVED	RESERVED	RESERVED	RESERVED	RESERVED	RESERVED	RESERVED	RESERVED
Register 18	12h	RESERVED	RESERVED	RESERVED	RESERVED	RESERVED	RESERVED	RESERVED	RESERVED
Register 19	13h	RATE3	RATE2	RATE1	RATE0	AMP3	AMP2	AMP1	AMP0
Register 20	14h	PD	DIS	GAIN1	GAIN0	TH3	TH2	TH1	TH0
Register 21	15h	RESERVED	RESERVED	RESERVED	RESERVED	RESERVED	RESERVED	RESERVED	RESERVED
Register 22	16h	RESERVED	RESERVED	RESERVED	RESERVED	RESERVED	RESERVED	RESERVED	RESERVED
Register 23	17h	RESERVED	RESERVED	RESERVED	RESERVED	RESERVED	RESERVED	RESERVED	RESERVED
Register 24	18h	RESERVED	RESERVED	RESERVED	RESERVED	RESERVED	RESERVED	RESERVED	RESERVED
Register 25	19h	RESERVED	RESERVED	RESERVED	RESERVED	RESERVED	RESERVED	RESERVED	RESERVED

7.6.1 Register Descriptions

This section describes the circuit functionality based on the register settings. Table 2 defines the various register bit field types used in this document.

Table 2. Register Bit Field Types

SYMBOL	DESCRIPTION	ACCESS, READ ACTION, WRITE VALUE
R	Read	Read-only
R/W	Read, write, or both	Read-write
W	Write	Write-only

7.6.2 Register 0: Control Settings (address = 00h) [reset = 0h]

Figure 15. Register 0

7	6	5	4	3	2	1	0
RESET	PD	RESERVED	RESERVED	RESERVED	RESERVED	RESERVED	PWRITE
W-0h	R/W-0h	R-Xh	R-Xh	R-Xh	R-Xh	R-Xh	R/W-0h

Table 3. Register 0 Field Descriptions

Bit	Field	Type	Reset	Description
7	RESET	W	0h	**Reset registers bit.** 1 = Resets all registers to default values 0 = Normal operation
6	PD	R/W	0h	**Power-down bit.** 1 = Power down all channels (I_{CC} is approximately 4 mA) 0 = Normal operation
5-1	Reserved	R	Undefined	Reserved. Read-only.
0	PWRITE	R/W	0h	**Parallel write mode bit.** 1 = Parallel write enabled (write register value to all channels) 0 = Serial write

7.6.3 Register 1: Amplitude and Rate for Channel 1 (address = 01h) [reset = 0h]

Figure 16. Register 1

7	6	5	4	3	2	1	0
RATE3	RATE2	RATE1	RATE0	AMP3	AMP2	AMP1	AMP0
R/W-0h	R/W-0h	R/W-0h	R/W-0h	R/W-0h	R/W-0h	R/W-0h	R/W-0h

Table 4. Register 1 Field Descriptions

Bit	Field	Type	Reset	Description
7-4	RATE[3 :0]	R/W	0h	**Rate adjustments bits for channel 1**. 0000 = 21 GHz (default) 0111 = BW decrease of approximately 0.4 GHz 1111 = BW increase of approximately 0.4 GHz All others: Do not use
3-0	AMP[3:0]	R/W	0h	**Amplitude adjustment bits for channel 1.** Table 5 lists the bit settings for AMP[3:0].

Table 5. AMP[3:0] Bit Settings

BITS	AMPLITUDE ADJUSTMENT (mV_{PP})	BITS	AMPLITUDE ADJUSTMENT (mV_{PP})
0000	0 (default)	1000	250
0001	50	1001	300
0010	100	1010	350
0011	150	1011	400
0100	200	1100	450
0101	250	1101	500
0110	300	1110	550
0111	350	1111	600

7.6.4 Register 2: Threshold and Gain for Channel 1 (address = 02h) [reset = 0h]

Figure 17. Register 2

7	6	5	4	3	2	1	0
PD	DIS	GAIN1	GAIN0	TH3	TH2	TH1	TH0
R/W-0h	R/W-0h	R/W-0h	R/W-0h	R/W-0h	R/W-0h	R/W-0h	R/W-0h

Table 6. Register 2 Field Descriptions

Bit	Field	Type	Reset	Description
7	PD	R/W	0h	**Power-down bit for channel 1**. 1 = Power down channel 1 0 = Normal operation
6	DIS	R/W	0h	**Disable output buffer for channel 1.** 1 = Disable channel 1 output buffer 0 = Normal operation
5-4	GAIN[1:0]	R/W	0h	**Gain adjustment bits for channel 1.** 00 = Default 01 = Do not use 10 = Medium (–4 dB) 11 = Minimum (–8 dB)
3-0	TH[3:0]	R/W	0h	**Threshold adjustment bits for channel 1**. 0000 = Zero shift 0001 = Minimum positive shift 0111 = Maximum positive shift 1000 = Zero shift 1001 = Minimum negative shift 1111 = Maximum negative shift

7.6.5 Register 7: Amplitude and Rate for Channel 2 (address = 07h) [reset = 0h]

Figure 18. Register 7

7	6	5	4	3	2	1	0
RATE3	RATE2	RATE1	RATE0	AMP3	AMP2	AMP1	AMP0
R/W-0h	R/W-0h	R/W-0h	R/W-0h	R/W-0h	R/W-0h	R/W-0h	R/W-0h

Table 7. Register 7 Field Descriptions

Bit	Field	Type	Reset	Description
7-4	RATE[3:0]	R/W	0h	**Rate adjustments bits for channel 2**. 0000 = 21 GHz (default) 0111 = BW decreases by approximately 0.4 GHz 1111 = BW increases by approximately 0.4 GHz
3-0	AMP[3:0]	R/W	0h	**Amplitude adjustment bits for channel 2.** Table 5 lists the bit settings for AMP[3:0].

7.6.6 Register 8: Threshold and Gain for Channel 1 (address = 08h) [reset = 0h]

Figure 19. Register 8

7	6	5	4	3	2	1	0
PD	DIS	GAIN1	GAIN0	TH3	TH2	TH1	TH0
R/W-0h	R/W-0h	R/W-0h	R/W-0h	R/W-0h	R/W-0h	R/W-0h	R/W-0h

Table 8. Register 8 Field Descriptions

Bit	Field	Type	Reset	Description
7	PD	R/W	0h	**Power-down bit for channel 2**. 1 = Power down channel 2 0 = Normal operation
6	DIS	R/W	0h	**Disable output buffer for channel 2.** 1 = Disable channel 2 output buffer 0 = Normal operation
5-4	GAIN[1:0]	R/W	0h	**Gain adjustment bits for channel 2.** 00 = Default 01 = Do not use 10 = Medium (–4 dB) 11 = Minimum (–8 dB)
3-0	TH[3:0]	R/W	0h	**Threshold adjustment bits for channel 2**. 0000 = Zero shift 0001 = Minimum positive shift 0111 = Maximum positive shift 1000 = Zero shift 1001 = Minimum negative shift 1111 = Maximum negative shift

7.6.7 Register 13: Amplitude and Rate for Channel 3 (address = 0Dh) [reset = 0h]

Figure 20. Register 13

7	6	5	4	3	2	1	0
RATE3	RATE2	RATE1	RATE0	AMP3	AMP2	AMP1	AMP0
R/W-0h	R/W-0h	R/W-0h	R/W-0h	R/W-0h	R/W-0h	R/W-0h	R/W-0h

Table 9. Register 13 Field Descriptions

Bit	Field	Type	Reset	Description
7-4	RATE[3:0]	R/W	0h	**Rate adjustments bits for channel 3**. 0000 = 21 GHz (default) 0111 = BW decreases by approximately 0.4 GHz 1111 = BW increases by approximately 0.4 GHz
3-0	AMP[3:0]	R/W	0h	**Amplitude adjustment bits for channel 3.** Table 5 lists the bit settings for AMP[3:0].

7.6.8 Register 14: Threshold and Gain for Channel 3 (address = 0Eh) [reset = 0h]

Figure 21. Register 14

7	6	5	4	3	2	1	0
PD	DIS	GAIN1	GAIN0	TH3	TH2	TH1	TH0
R/W-0h	R/W-0h	R/W-0h	R/W-0h	R/W-0h	R/W-0h	R/W-0h	R/W-0h

Table 10. Register 14 Field Descriptions

Bit	Field	Type	Reset	Description
7	PD	R/W	0h	**Power-down bit for channel 3**. 1 = Power down channel 3 0 = Normal operation
6	DIS	R/W	0h	**Disable output buffer for channel 3.** 1 = Disable channel 3 output buffer 0 = Normal operation
5-4	GAIN[1:0]	R/W	0h	**Gain adjustment bits for channel 3.** 00 = Default 01 = Do not use 10 = Medium (–4 dB) 11 = Minimum (–8 dB)
3-0	TH[3:0]	R/W	0h	**Threshold adjustment bits for channel 3**. 0000 = Zero shift 0001 = Minimum positive shift 0111 = Maximum positive shift 1000 = Zero shift 1001 = Minimum negative shift 1111 = Maximum negative shift

7.6.9 Register 19: Amplitude and Rate for Channel 4 (address = 13h) [reset = 0h]

Figure 22. Register 19

7	6	5	4	3	2	1	0
RATE3	RATE2	RATE1	RATE0	AMP3	AMP2	AMP1	AMP0
R/W-0h	R/W-0h	R/W-0h	R/W-0h	R/W-0h	R/W-0h	R/W-0h	R/W-0h

Table 11. Register 19 Field Descriptions

Bit	Field	Type	Reset	Description
7-4	RATE[3:0]	R/W	0h	**Rate adjustments bits for channel 4**. 0000 = 21 GHz (default) 0111 = BW decreases by approximately 0.4 GHz 1111 = BW increases by approximately 0.4 GHz
3-0	AMP[3:0]	R/W	0h	**Amplitude adjustment bits for channel 4.** Table 5 lists the bit settings for AMP[3:0].

7.6.10 Register 20: Threshold and Gain for Channel 4 (address = 14h) [reset = 0h]

Figure 23. Register 20

7	6	5	4	3	2	1	0
PD	DIS	GAIN1	GAIN0	TH3	TH2	TH1	TH0
R/W-0h	R/W-0h	R/W-0h	R/W-0h	R/W-0h	R/W-0h	R/W-0h	R/W-0h

Table 12. Register 20 Field Descriptions

Bit	Field	Type	Reset	Description
7	PD	R/W	0h	**Power-down bit for channel 4**. 1 = Power down channel 4 0 = Normal operation
6	DIS	R/W	0h	**Disable output buffer for channel 4.** 1 = Disable channel 4 output buffer 0 = Normal operation
5-4	GAIN[1:0]	R/W	0h	**Gain adjustment bits for channel 4.** 00 = Default 01 = Do not use 10 = Medium (–4 dB) 11 = Minimum (–8 dB)
3-0	TH[3:0]	R/W	0h	**Threshold adjustment bits for channel 4**. 0000 = Zero shift 0001 = Minimum positive shift 0111 = Maximum positive shift 1000 = Zero shift 1001 = Minimum negative shift 1111 = Maximum negative shift

8 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

8.1 Application Information

Figure 24 shows the ONET2804TLP being used in a fiber optic receiver application with four channels running at 25 Gbps each and with pin control. Figure 27 illustrates the device being used with two-wire control. The ONET2804TLP converts the electrical current generated by the PIN photodiode into a differential output voltage. The FILTERx inputs provide a DC bias voltage for the PIN that is low-pass filtered. The photodiode must be connected to the FILTERx pads for the bias circuit to function correctly because the voltage drop across the photodiode FET is sensed and used by the bias circuit.

The RSSIx outputs are used to mirror the photodiode output current and can be connected via resistors to GND. The voltage gain can be adjusted for the intended application by choosing the external resistor; however, for proper operation of the ONET2804TLP, ensure that the voltage at RSSIx never exceeds V_{CC} – 0.65 V. If the RSSIx outputs are not used when using the internal PD bias, then leave these outputs open.

The OUTx+ and OUTx– pins are internally terminated by 50-Ω pullup resisters to V_{CC}. The outputs must be AC coupled (for example, by using 0.1-µF capacitors) to the succeeding device.

8.2 Typical Applications

8.2.1 Pad Control Application

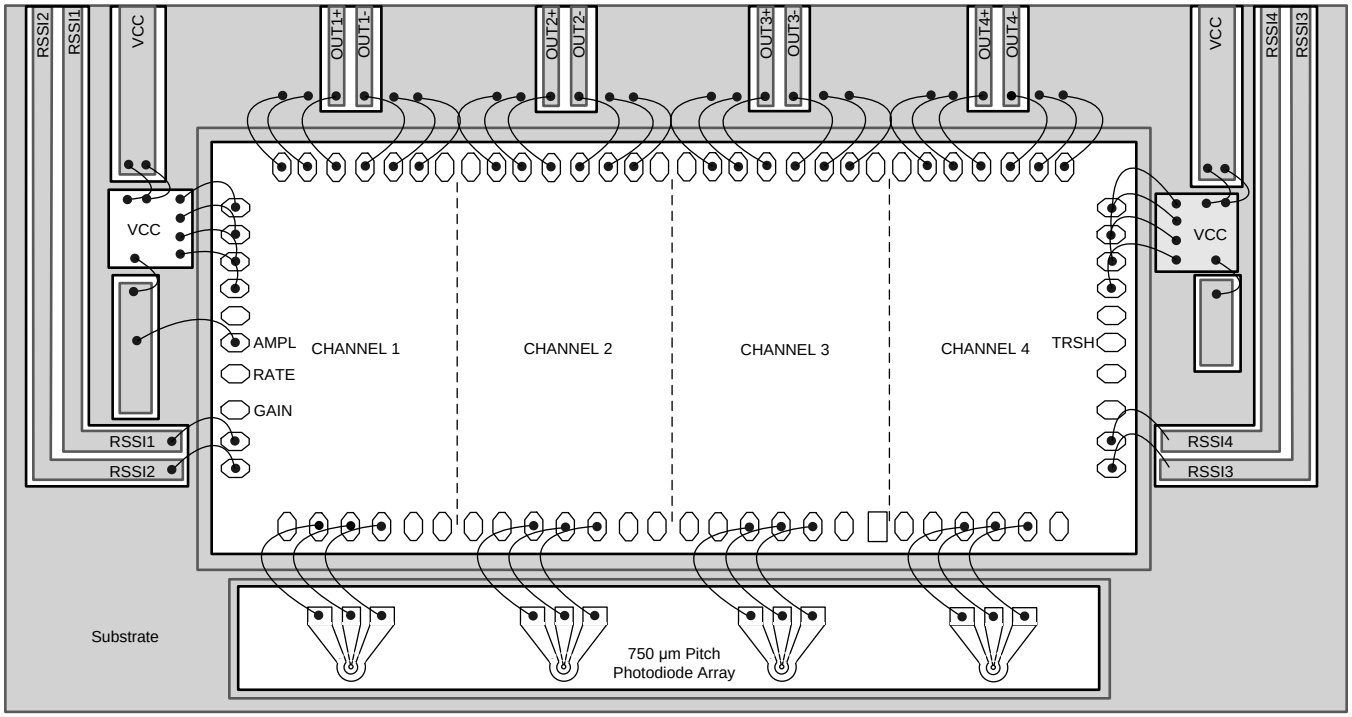


Figure 24. Basic Application Circuit with Pad Control

Typical Applications (continued)

8.2.1.1 Design Requirements

Table 13. Design Parameters

PARAMETER	VALUE
Input voltage	3.3 V
Output voltage	300 mV_{PP}

8.2.1.2 Detailed Design Procedure

The ONET2804TLP is designed to be used in conjunction with a 750-μm pitch photodiode array or individual photodiodes and assembled into a receiver optical subassembly (ROSA). The TIA is typically mounted on a ceramic substrate with etched connections for V_{CC}, RSSIx, and 100-Ω differential transmission lines for the output voltage. The photodiode converts the optical input signal into a current that is supplied to the TIA through wire bonds. The TIA then converts the input current into a voltage and further amplifies the signal. TI recommends setting the output amplitude to the 300-mV_{PP} level by leaving AMPL (pad 6) floating.

The ROSA is typically mounted on a printed circuit board (PCB) with 100-Ω differential transmission lines and RF connectors [such as GPPO® or 2.4-mm subminiature version A (SMA) connectors]. When measuring the output from the ROSA mounted on the PCB, the frequency dependent loss of the transmission lines affects the frequency response. The loss can be de-embedded from the measurement to determine the actual frequency response at the output of the ROSA.

8.2.1.3 Application Curves

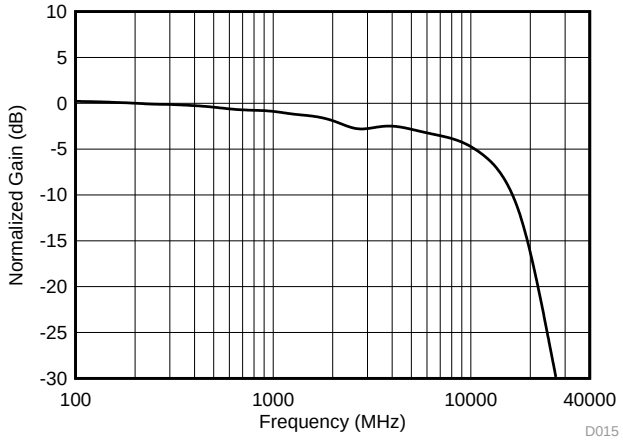


Figure 25. Gain vs Frequency (Without De-Embedding)

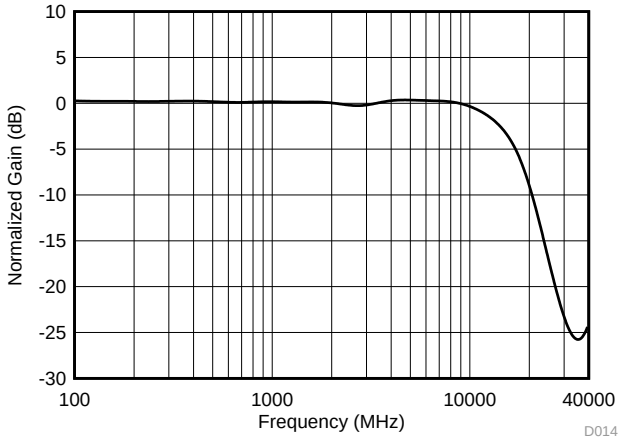


Figure 26. Gain vs Frequency (With De-Embedding)

8.2.2 Two-Wire Control Application

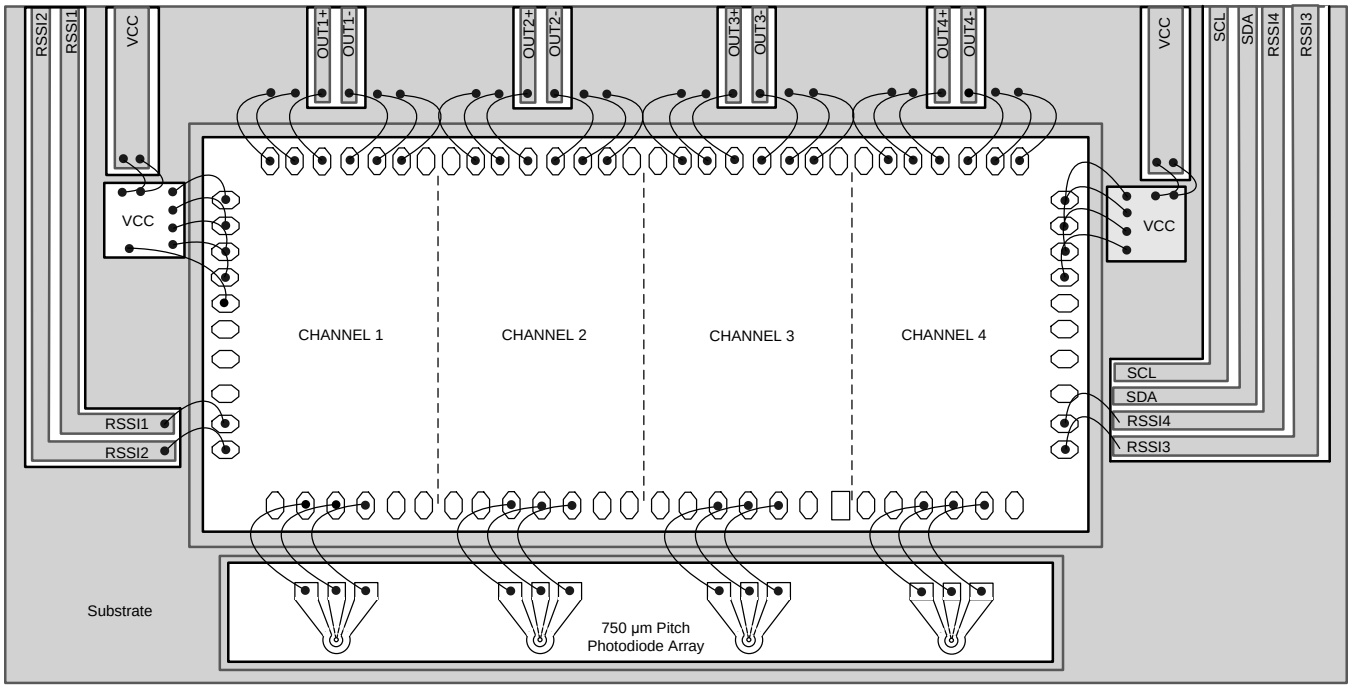


Figure 27. Basic Application Circuit with Two-Wire Control

8.2.2.1 Design Requirements

Table 14 lists the design requirements for this application.

Table 14. Design Parameters

PARAMETER	VALUE
I2CENA pin voltage	3.3 V
Output voltage	300 mV_{PP}

8.2.2.2 Detailed Design Procedure

As described in the *Detailed Design Procedure* section on the pad control application, TI generally recommends setting the output voltage of the device to the 300-mV_{PP} setting. The output voltage setting can be controlled by bonding specific device pads as detailed in the *Pad Control Application* section, but can alternatively be controlled using the device I^2C interface. To set the output amplitude via the I^2C interface, the I2CENA pad must be connected to V_{CC}, which enables the I^2C control and disables pad control. The output amplitude can then be set to the 300-mV_{PP} mode by writing the value 0110 to bits[3:0] of the amplitude control registers for each channel as described in the *Register Maps* section. Requirements to operate the I^2C interface are detailed in the *Programming* section.

9 Power Supply Recommendations

The ONET2804TLP is designed to operate from an input supply voltage range between 2.8 V and 3.47 V. There are a total of eight power-supply pads (V_{CC}I[4:1] and V_{CC}O[4:0]) that must be connected for proper operation. V_{CC}I[4:1] are used to supply power to the input transimpedance amplifier stages and V_{CC}O[4:1] are used to supply power to the voltage amplifiers and output buffers. Each amplifier is powered up separately but there are some common internal connections for support circuitry (such as the two-wire interface). Therefore, if only one channel is being evaluated, all eight supply pads must be connected. Use two single-layer ceramic (SLC) capacitors in the range of 270 pF to 680 pF for power-supply decoupling. V_{CC}I1, V_{CC}I2, V_{CC}O1, and V_{CC}O2 should be bonded to one capacitor and V_{CC}I3, V_{CC}I4, V_{CC}O3, and V_{CC}O4 should be bonded to the other capacitor; see Figure 24 and Figure 27 for reference.

10 Layout

10.1 Layout Guidelines

Careful attention to assembly parasitics and external components is necessary to achieve optimal performance.

- Minimize the total capacitance on the INx pad by using a low capacitance photodiode (100 fF) and pay attention to stray capacitances. Place the photodiode close to the ONET2804TLP die and keep the wire bond inductance in the range of 300 pH to 400 pH.
- Use identical termination and symmetrical transmission lines at the AC-coupled differential output pins (OUTx+ and OUTx–).
- Use short bond wire connections for the supply pins V_{CC}Ix, V_{CC}Ox, and GND. Supply voltage filtering is provided on-chip but filtering can be improved by using an additional external capacitor.
- The die has backside metal and conductive epoxy must be used to attach the die to ground.

10.2 Layout Example

The device dimensions are shown in Figure 28 and Table 15 provides the pad locations. The device is designed for wire bonding not flip chip layouts.

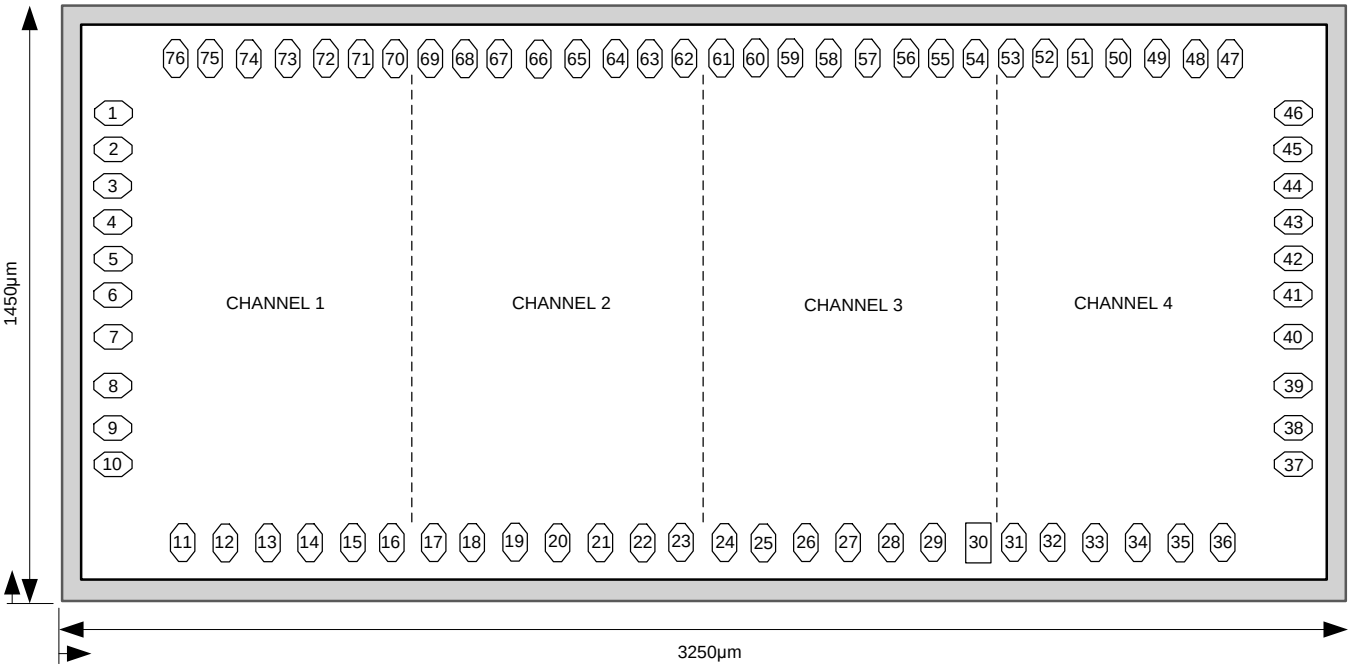


Figure 28. Device Dimensions and Pad Locations

Die thickness: 203 µm ± 13 µm
Pad dimensions: 105 µm × 65 µm
Die size: 3250 µm ± 40 µm × 1450 µm ± 40 µm

Layout Example (continued)

Table 15. Bond Pad Coordinates

PAD	COORDINATES (Referenced to Pad 1)		SYMBOL	TYPE	DESCRIPTION
	X (µm)	Y (µm)			
1	0	0	$V_{CC}O1$	Supply	3.3-V supply voltage
2	0	–94	$V_{CC}O2$	Supply	3.3-V supply voltage
3	0	–188	$V_{CC}I2$	Supply	3.3-V supply voltage
4	0	–282	$V_{CC}I1$	Supply	3.3-V supply voltage
5	0	–376	I2CENA	Digital input	I^2C enable
6	0	–470	AMPL	Digital input	Amplitude control
7	0	–580	RATE	Digital input	Rate selection
8	0	–704	GAIN	Digital input	Gain control
9	0	–814	RSSI1	Analog output	Receiver signal strength indicator for channel 1
10	0	–908	RSSI2	Analog output	Receiver signal strength indicator for channel 2
11	180	–1110	GND	Supply	Circuit ground
12	290	–1110	FILTER1	Analog output	Bias voltage for photodiode 1
13	400	–1110	IN1	Analog input	TIA input for channel 1
14	510	–1110	FILTER1	Analog output	Bias voltage for photodiode 1
15	620	–1110	GND	Supply	Circuit ground
16	720	–1110	NC	No connection	Do not connect
17	829	–1110	NC	No connection	Do not connect
18	929	–1110	GND	Supply	Circuit ground
19	1039	–1110	FILTER2	Analog output	Bias voltage for photodiode 2
20	1149	–1110	IN2	Analog input	TIA input for channel 2
21	1259	–1110	FILTER2	Analog output	Bias voltage for photodiode 2
22	1369	–1110	GND	Supply	Circuit ground
23	1469	–1110	NC	No connect	Do not connect
24	1580	–1110	NC	No connect	Do not connect
25	1680	–1110	GND	Supply	Circuit ground
26	1790	–1110	FILTER3	Analog output	Bias voltage for photodiode 3
27	1900	–1110	IN3	Analog input	TIA input for channel 3
28	2010	–1110	FILTER3	Analog output	Bias voltage for photodiode 3
29	2120	–1110	GND	Supply	Circuit ground
30	2239	–1110	NC	No connect	Do not connect
31	2329	–1110	NC	No connect	Do not connect
32	2429	–1110	GND	Supply	Circuit ground
33	2539	–1110	FILTER4	Analog output	Bias voltage for photodiode 4
34	2649	–1110	IN4	Analog input	TIA input for channel 4
35	2759	–1110	FILTER4	Analog output	Bias voltage for photodiode 4
36	2869	–1110	GND	Supply	Circuit ground
37	3051	–908	RSSI3	Analog output	Receiver signal strength indicator for channel 3
38	3051	–814	RSSI4	Analog output	Receiver signal strength indicator for channel 4
39	3051	–704	SDA	Digital input/output	2-wire data
40	3051	–579	SCL	Digital input	2-wire clock
41	3051	–470	TRSH	Digital input	Input threshold control (cross-point)
42	3051	–376	NC	No connect	Do not connect
43	3051	–282	$V_{CC}I4$	Supply	3.3-V supply voltage
44	3051	–188	$V_{CC}I3$	Supply	3.3-V supply voltage

Layout Example (continued)

Table 15. Bond Pad Coordinates (continued)

PAD	COORDINATES (Referenced to Pad 1)		SYMBOL	TYPE	DESCRIPTION
	X (µm)	Y (µm)			
45	3051	–94	$V_{CC}O3$	Supply	3.3-V supply voltage
46	3051	0	$V_{CC}O4$	Supply	3.3-V supply voltage
47	2888	140	GND	Supply	Circuit ground
48	2799	140	GND	Supply	Circuit ground
49	2699	140	OUT4–	Analog output	Inverted data output for channel 4
50	2599	140	OUT4+	Analog output	Noninverted data output for channel 4
51	2499	140	GND	Supply	Circuit ground
52	2410	140	GND	Supply	Circuit ground
53	2322	140	ADR1	Digital input	2-wire address bit 1 control
54	2228	140	ADR0	Digital input	2-wire address bit 0 control
55	2139	140	GND	Supply	Circuit ground
56	2050	140	GND	Supply	Circuit ground
57	1950	140	OUT3–	Analog output	Inverted data output for channel 3
58	1850	140	OUT3+	Analog output	Noninverted data output for channel 3
59	1750	140	GND	Supply	Circuit ground
60	1661	140	GND	Supply	Circuit ground
61	1572	140	NC	No connection	Do not connect
62	1477	140	NC	No connection	Do not connect
63	1388	140	GND	Supply	Circuit ground
64	1299	140	GND	Supply	Circuit ground
65	1199	140	OUT2–	Analog output	Inverted data output for channel 2
66	1099	140	OUT2+	Analog output	Noninverted data output for channel 2
67	999	140	GND	Supply	Circuit ground
68	910	140	GND	Supply	Circuit ground
69	821	140	NC	No connect	Do not connect
70	728	140	NRESET	Digital input	2-wire negative reset
71	639	140	GND	Supply	Circuit ground
72	550	140	GND	Supply	Circuit ground
73	450	140	OUT1–	Analog output	Inverted data output for channel 1
74	350	140	OUT1+	Analog output	Noninverted data output for channel 1
75	250	140	GND	Supply	Circuit ground
76	161	140	GND	Supply	Circuit ground

11 Device and Documentation Support

11.1 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on *Alert me* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

11.2 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E™ Online Community ***TI's Engineer-to-Engineer (E2E) Community.*** Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support ***TI's Design Support*** Quickly find helpful E2E forums along with design support tools and contact information for technical support.

11.3 Trademarks

E2E is a trademark of Texas Instruments.
GPPO is a registered trademark of Gilbert Incorporated.
All other trademarks are the property of their respective owners.

11.4 Electrostatic Discharge Caution

This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

11.5 Glossary

SLYZ022 — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

12 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
ONET2804TLPY	ACTIVE	DIESALE	Y	0	135	TBD	Call TI	Call TI	-40 to 100		Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".
RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.
Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

IMPORTANT NOTICE AND DISCLAIMER

TI PROVIDES TECHNICAL AND RELIABILITY DATA (INCLUDING DATASHEETS), DESIGN RESOURCES (INCLUDING REFERENCE DESIGNS), APPLICATION OR OTHER DESIGN ADVICE, WEB TOOLS, SAFETY INFORMATION, AND OTHER RESOURCES “AS IS” AND WITH ALL FAULTS, AND DISCLAIMS ALL WARRANTIES, EXPRESS AND IMPLIED, INCLUDING WITHOUT LIMITATION ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS.

These resources are intended for skilled developers designing with TI products. You are solely responsible for (1) selecting the appropriate TI products for your application, (2) designing, validating and testing your application, and (3) ensuring your application meets applicable standards, and any other safety, security, or other requirements. These resources are subject to change without notice. TI grants you permission to use these resources only for development of an application that uses the TI products described in the resource. Other reproduction and display of these resources is prohibited. No license is granted to any other TI intellectual property right or to any third party intellectual property right. TI disclaims responsibility for, and you will fully indemnify TI and its representatives against, any claims, damages, costs, losses, and liabilities arising out of your use of these resources.

TI’s products are provided subject to TI’s Terms of Sale (www.ti.com/legal/termsofsale.html) or other applicable terms available either on ti.com or provided in conjunction with such TI products. TI’s provision of these resources does not expand or otherwise alter TI’s applicable warranties or warranty disclaimers for TI products.

Mailing Address: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265